















SN74AUC1G125

SCES382L -MARCH 2002-REVISED JUNE 2017

SN74AUC1G125 Single Bus Buffer Gate With 3-State Output

Features

- Latch-Up Performance Exceeds 100 mA Per JESD 78. Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Available in the Texas Instruments NanoFree™ Package
- Optimized for 1.8-V Operation and Is 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation
- Ioff Supports Partial Power Down Mode and Back **Drive Protection**
- Sub-1-V Operable
- Max t_{pd} of 2.5 ns at 1.8 V
- Low Power Consumption, 10-µA Maximum I_{CC}
- ±8-mA Output Drive at 1.8 V

Applications

- **AV Receiver**
- Audio Dock: Portable
- Blu-Ray Player and Home Theater
- Embedded PC
- MP3 Player/Recorder (Portable Audio)
- Personal Digital Assistant (PDA)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drive (SSD): Client and Enterprise
- TV: LCD/Digital and High-Definition (HDTV)
- Tablet: Enterprise
- Video Analytics: Server
- Wireless Headset, Keyboard, and Mouse

3 Description

This bus buffer gate is operational at 0.8-V to 2.7-V V_{CC}, but is designed specifically for 1.65-V to 1.95-V V_{CC} operation.

The SN74AUC1G125 device is a single line driver with a 3-state output. The output is disabled when the output-enable (OE) input is high.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using $I_{\rm off}$. The $I_{\rm off}$ circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	RT NUMBER PACKAGE			
SN74AUC1G125DBV	SOT-23 (5)	2.90 mm × 1.60 mm		
SN74AUC1G125DCK	SC70 (5)	2.00 mm x 1.25 mm		
SN74AUC1G125YZP	DSBGA (5)	1.75 mm × 1.25 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

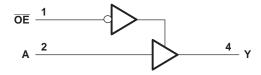




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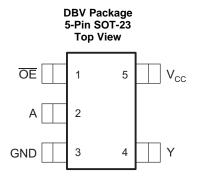
4 Revision History

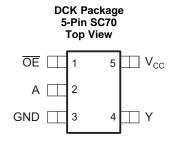
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

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•	section, Device Functional Modes, Device and Documentation Support section, and Mechanical, Packaging, and	1
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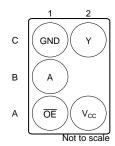


5 Pin Configuration and Functions









NC – No internal connection
See mechanical drawings for dimensions.

Pin Functions

	PIN		1/0	DESCRIPTION			
NAME	DBV, DCK	YZP	I/O	DESCRIPTION			
Α	2	B1	I	Logic input			
GND	3	C1	_	Ground			
ŌĒ	1	A1	I	Active-low output enable			
V _{CC}	5	A2	_	Positive supply			
Υ	4	C2	0	Output			

Product Folder Links: SN74AUC1G125



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	3.6	V
VI	Input voltage ⁽²⁾			3.6	V
Vo	Voltage range applied to any output in the high-impedance or power-off state $^{(2)}$			3.6	V
Vo	Output voltage range ⁽²⁾	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±20	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	1000	V
		Machine Model (A115-A)	200	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		0.8	2.7	V
		V _{CC} = 0.8 V	V _{CC}		
V_{IH}	High-level input voltage	V _{CC} = 1.1 V to 1.95 V	0.65 × V _{CC}		V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		
		V _{CC} = 0.8 V		0	
V_{IL}	Low-level input voltage	V _{CC} = 1.1 V to 1.95 V		$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	
V_{I}	Input voltage		0	3.6	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 0.8 V		-0.7	
		V _{CC} = 1.1 V		-3	
I_{OH}	High-level output current	V _{CC} = 1.4 V		- 5	mA
		V _{CC} = 1.65 V		-8	
		V _{CC} = 2.3 V		-9	
		V _{CC} = 0.8 V		0.7	
		V _{CC} = 1.1 V		3	
I _{OL}	Low-level output current	V _{CC} = 1.4 V		5	mA
		V _{CC} = 1.65 V		8	
		V _{CC} = 2.3 V		9	

All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See Implications of Slow or Floating CMOS Inputs, SCBA004.

Product Folder Links: SN74AUC1G125

²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Recommended Operating Conditions (continued)

See (1)

			MIN	MAX	UNIT
		$V_{CC} = 0.8 \text{ V to } 1.6 \text{ V}$		20	
$\Delta t/\Delta v$	Input transition rise or fall rate	V _{CC} = 1.65 V to 1.95 V		10	ns/V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		3	
T _A	Operating free-air temperature		-40	85	°C

6.4 Thermal Information

			SN74AUC1G125					
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	YZP (DSBGA)	UNIT			
		5 PINS	5 PINS	5 PINS				
$R_{\theta JA}$	Junction-to-ambient thermal resistance	206	252	132	°C/W			

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETE	ER	TEST CO	NDITIONS		V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT	
		I _{OH} = -100 μA			0.8 V to 2.7 V	V _{CC} - 0.1				
		$I_{OH} = -0.7 \text{ mA}$			0.8 V		0.55			
V _{OH}	$I_{OH} = -3 \text{ mA}$			1.1 V	0.8			V		
	$I_{OH} = -5 \text{ mA}$			1.4 V	1			V		
		$I_{OH} = -8 \text{ mA}$			1.65 V	1.2				
		$I_{OH} = -9 \text{ mA}$			2.3 V	1.8				
		$I_{OL} = 100 \mu A$			0.8 V to 2.7 V			0.2		
V		$I_{OL} = 0.7 \text{ mA}$			0.8 V		0.25			
	$I_{OL} = 3 \text{ mA}$			1.1 V			0.3	.3 _V		
V _{OL}		I _{OL} = 5 mA			1.4 V			0.4	V	
		$I_{OL} = 8 \text{ mA}$			1.65 V			0.45		
		$I_{OL} = 9 \text{ mA}$			2.3 V			0.6		
I _I A or \overline{OE}	E input	$V_I = V_{CC}$ or GND			0 to 2.7 V			±5	μΑ	
l _{off}		V_I or $V_O = 2.7 V$			0			±10	μΑ	
l _{OZ}		$V_O = V_{CC}$ or GND			2.7 V			±10	μΑ	
I _{CC}		$V_I = V_{CC}$ or GND,	I _O = 0		0.8 V to 2.7 V			10	μΑ	
C _I		$V_I = V_{CC}$ or GND			2.5 V		2.5		pF	
Co		$V_O = V_{CC}$ or GND			2.5 V		5.5		pF	

⁽¹⁾ All typical values are at $T_A = 25$ °C.

6.6 Switching Characteristics: $C_L = 15 pF$

over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 1)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V _{CC} = 0.8 V	V _{CC} = ± 0.		V _{CC} = ± 0.			_C = 1.8 : 0.15 V		V _{CC} = ± 0.		UNIT
	(INPUT)	(001701)	TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX		
	t _{pd}	Α	Υ	4.7	0.8	3.6	0.4	2.3	0.6	1	1.5	0.5	1.3	ns
	t _{en}	ŌĒ	Υ	5.4	0.7	4.1	0.5	2.6	0.6	1.1	1.8	0.5	1.4	ns
	t _{dis}	ŌĒ	Υ	4.8	1.4	4.3	1.4	4	1.5	2.2	2.9	0.9	2.2	ns

Product Folder Links: SN74AUC1G125



6.7 Switching Characteristics: $C_L = 30 pF$

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	TO	V _C	_C = 1.8 : 0.15 \	, ,	V _{CC} = ± 0.	2.5 V 2 V	UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MAX	MIN	MAX	
t_{pd}	Α	Υ	0.7	1.5	2.5	0.9	1.7	ns
t _{en}	ŌE	Υ	1	1.6	2.6	1.1	1.9	ns
t _{dis}	ŌE	Υ	1.8	2.2	3.1	8.0	1.7	ns

6.8 Operating Characteristics

 $T_A = 25$ °C

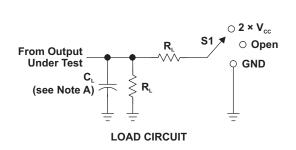
PARAMETER			TEST CONDITIONS	V _{CC} = 0.8 V TYP	V _{CC} = 1.2 V TYP	V _{CC} = 1.5 V TYP	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	UNIT
C _{pd}	Power	Outputs enabled	f 40 MHz	14	14	14	15	16	~F
	dissipation capacitance	Outputs disabled	f = 10 MHz	1.5	1.5	1.5	2	2.5	pF

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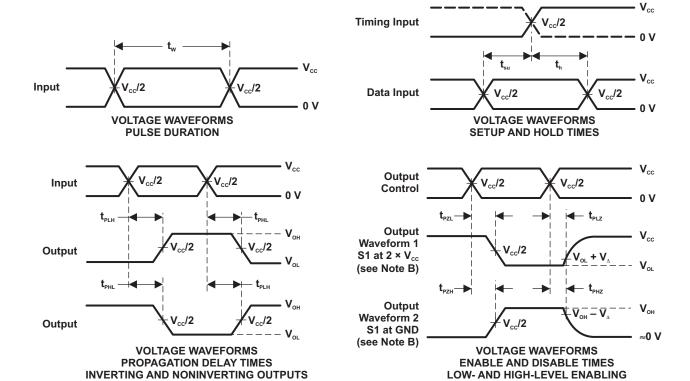


Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V _{cc}
t _{PHZ} /t _{PZH}	GND

V _{cc}	C _L	R _L	V _Δ
0.8 V	15 pF	2 k Ω	0.1 V
1.2 V ± 0.1 V	15 pF	2 k Ω	0.1 V
1.5 V ± 0.1 V	15 pF	2 k Ω	0.1 V
1.8 V ± 0.15 V	15 pF	2 k Ω	0.15 V
2.5 V ± 0.2 V	15 pF	2 kΩ	0.15 V
1.8 V ± 0.15 V	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	30 pF	500 Ω	0.15 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: $PRR \le 10 \text{ MHz}$, $Z_{\circ} = 50 \Omega$,
- slew rate ≥ 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. $\,t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. t_{PLH} and t_{PHL} are the same as t_{pol}

Figure 1. Load Circuit and Voltage Waveforms

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8 Detailed Description

8.1 Functional Block Diagram

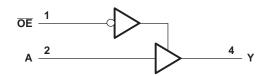


Figure 2. Logic Diagram (Positive Logic)

8.2 Device Functional Modes

Table 1 lists the functional modes of the SN74AUC1G125.

Table 1. Function Table

INP	UTS	OUTPUT
ŌĒ	Α	Y
L	Н	Н
L	L	L
Н	X	Z

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9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

9.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74AUC1G125DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U25R	Samples
74AUC1G125DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U25R	Samples
74AUC1G125DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(UM5, UMF, UMR)	Samples
74AUC1G125DCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(UM5, UMF, UMR)	Samples
SN74AUC1G125DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U25R	Samples
SN74AUC1G125DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(UM5, UMF, UMR)	Samples
SN74AUC1G125YZPR	ACTIVE	DSBGA	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	UMN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

6-Feb-2020

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AUC1G125:

Enhanced Product: SN74AUC1G125-EP

NOTE: Qualified Version Definitions:

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC1G125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1G125DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AUC1G125DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AUC1G125DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AUC1G125YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

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*All dimensions are nominal

All difficultions are norminal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC1G125DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AUC1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G125DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AUC1G125YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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